

FINAL PRODUCT/PROCESS CHANGE NOTIFICATION #16480

Generic Copy

09-Jul-2010

<u>TITLE:</u> Final Notification for Capacity Expansion Qualification of ON Semiconductor Roznov, Czech Republic Wafer Fab (CZ4) for HD Plus Currently Fabricated at ON Semiconductor's Aizu Japan Wafer Fab

PROPOSED FIRST SHIP DATE: 09-Oct-2010

AFFECTED CHANGE CATEGORY(S): ON Semi Fab Site

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact your local ON Semiconductor Sales Office or Suem Loo < Suem.Loo@onsemi.com > or Wes Reid < wes.reid@onsemi.com >

<u>SAMPLES:</u> Contact your local ON Semiconductor Sales Office or Suem Loo < Suem.loo@onsemi.com >

<u>ADDITIONAL RELIABLITY DATA:</u> Available. Contact your local ON Semiconductor Sales Office or Donna Scheuch < d.scheuch@onsemi.com >

NOTIFICATION TYPE:

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 90 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <quality@onsemi.com>.

DESCRIPTION AND PURPOSE:

This FPCN is a follow up from IPCN #16450. ON Semiconductor is notifying customers that these HD Plus process products are now fabricated in ON Semiconductor's CZ4 wafer fabrication facility in Roznov, Czech Republic. Upon expiration of the associated Final PCN(s), devices may be supplied from either the Aizu or CZ4 wafer fab.

The HD Plus processes are now qualified at the CZ4 wafer fab. No die design or process changes were occurred. No changes to packaging were occurred as a result of this wafer fab qualification.

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RELIABILITY DATA SUMMARY:

QUALIFICATION PLAN

A full qualification and reliability testing were performed on a qualification vehicle <u>NIS5132MN1TXG</u>, which was chosen based on highest voltage.

Reliability Test Results of NIS5132MN1TXG:

#	Test	Test Conditions	Read points	Sample Size	Results
1	AC-PC	Ta = 121°C/ 100% RH/ 15psig	Test @ 96hrs	3 lots x 77 units	0 / 231
2	HAST-PC	130°C/85% RH for 96 hrs	Test @ 96hrs	3 lots x 77 units	0 / 231
3	HTOL	TA = 125°C for 504hrs	Test @ 504 Hrs	3 lots x 77 units	0 / 231
4	HTRB	TA = 125°C for 504hrs	Test @ 504 Hrs	3 lots x 77 units	0 / 231
5	HTSL	TA = 150°C for 504hrs	Test @ 504 Hrs	3 lots x 77 units	0 / 231
6	TC-PC	-65°C to +150°C for 500 cycles	Test @ 500 cycles	3 lots x 77 units	0 / 231

ELECTRICAL CHARACTERISTIC SUMMARY:

Data are available upon request. Contact Suem Loo < Suem.Loo@onsemi.com >

CHANGED PART IDENTIFICATION:

Affected products from ON Semiconductor with date code marking starting WW39 and greater may be sourced from either the Aizu Wafer Fab in Japan or the CZ4 Wafer fab in Roznov, Czech Republic.

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List of affected General Parts:

NIS5132MN1TXG NIS5135MN1TXG

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